

A Yu Kuznetsov

List of Publications by Year in descending order

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196
papers

5,023
citations

109321

35
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118850

62
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198
all docs

198
docs citations

198
times ranked

5348
citing authors

#	ARTICLE	IF	CITATIONS
1	Disorder-Induced Ordering in Gallium Oxide Polymorphs. <i>Physical Review Letters</i> , 2022, 128, 015704.	7.8	36
2	Formation of carbon interstitial-related defect levels by thermal injection of carbon into n -type $4H$ -SiC. <i>Journal of Applied Physics</i> , 2022, 131, .	2.5	7
3	Radiation-induced defect accumulation and annealing in Si-implanted gallium oxide. <i>Journal of Applied Physics</i> , 2022, 131, .	2.5	17
4	Photoluminescence intensity of Cu-doped ZnO modulated via defect occupancy by applying electric bias. <i>Journal Physics D: Applied Physics</i> , 2022, 55, 315102.	2.8	2
5	Efficient, recyclable, and affordable daylight induced Cu/Cu ₂ O/CuI photocatalyst via an inexpensive iodine sublimation process. <i>Applied Surface Science</i> , 2021, 537, 147007.	6.1	14
6	Radiation and Emission in Materials: Similarity of Principles and Multi-Functional Applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2000772.	1.8	0
7	Broad Diversity of Near-Infrared Single-Photon Emitters in Silicon. <i>Physical Review Letters</i> , 2021, 126, 083602.	7.8	48
8	Correlations of thermal properties with grain structure, morphology, and defect balance in nanoscale polycrystalline ZnO films. <i>Applied Surface Science</i> , 2021, 546, 149095.	6.1	11
9	ZnSnN ₂ in Real Space and k -Space: Lattice Constants, Dislocation Density, and Optical Band Gap. <i>Advanced Optical Materials</i> , 2021, 9, 2100015.	7.3	10
10	Dominating migration barrier for intrinsic defects in gallium oxide: Dose-rate effect measurements. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	15
11	Resolving Jahn-Teller induced vibronic fine structure of silicon vacancy quantum emission in silicon carbide. <i>Physical Review B</i> , 2021, 104, .	3.2	2
12	Fermi level controlled point defect balance in ion irradiated indium oxide. <i>Journal of Applied Physics</i> , 2021, 130, 085703.	2.5	4
13	Carbon vacancy control in p^{++} - n silicon carbide diodes for high voltage bipolar applications. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 455106.	2.8	3
14	Activation energy of silicon diffusion in gallium oxide: Roles of the mediating defects charge states and phase modification. <i>Applied Physics Letters</i> , 2021, 119, .	3.3	6
15	Fine structure in electronic transitions attributed to nitrogen donor in silicon carbide. <i>Applied Physics Letters</i> , 2021, 119, 262101.	3.3	1
16	Al incorporation during metal organic chemical vapour deposition of aluminium zinc oxide. <i>Thin Solid Films</i> , 2020, 709, 138245.	1.8	3
17	Strain Modulation of Si Vacancy Emission from SiC Micro- and Nanoparticles. <i>Nano Letters</i> , 2020, 20, 8689-8695.	9.1	11
18	Single artificial atoms in silicon emitting at telecom wavelengths. <i>Nature Electronics</i> , 2020, 3, 738-743.	26.0	72

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19	Acceptor complex signatures in oxygen-rich ZnO thin films implanted with chlorine ions. Journal of Applied Physics, 2020, 128, .	2.5	5
20	Impact of chloride surface treatment on nano-porous GaN structure for enhanced water-splitting efficiency. Applied Surface Science, 2020, 532, 147465.	6.1	28
21	High electron mobility single-crystalline ZnSn ₂ on ZnO (0001) substrates. CrystEngComm, 2020, 22, 6268-6274.	2.6	13
22	Studying Properties of Defects. , 2020, , 1-20.		0
23	Effects of annealing on photoluminescence and defect interplay in ZnO bombarded by heavy ions: Crucial role of the ion dose. Journal of Applied Physics, 2020, 127, 025701.	2.5	5
24	Experimental exploration of the amphoteric defect model by cryogenic ion irradiation of a range of wide band gap oxide materials. Journal of Physics Condensed Matter, 2020, 32, 415704.	1.8	7
25	Generation and metastability of deep level states in $\hat{\Gamma}^2$ -Ga ₂ O ₃ exposed to reverse bias at elevated temperatures. Journal of Applied Physics, 2019, 125, 185706.	2.5	13
26	Evidence of defect band mechanism responsible for band gap evolution in ZnO alloys. Physical Review B, 2019, 100, .		
27	Energetics, migration and trapping of Zn interstitials in ZnO. Journal Physics D: Applied Physics, 2019, 52, 485103.	2.8	0
28	Defect annealing kinetics in ZnO implanted with Zn substituting elements: Zn interstitials and Li redistribution. Journal of Applied Physics, 2019, 125, .	2.5	8
29	Impact of proton irradiation on conductivity and deep level defects in $\hat{\Gamma}^2$ -Ga ₂ O ₃ . APL Materials, 2019, 7, .	5.1	143
30	Bandgap bowing in crystalline (ZnO) _{1-x} (GaN) _x thin films; influence of composition and structural properties. Semiconductor Science and Technology, 2019, 34, 015001.	2.0	7
31	Iron and intrinsic deep level states in Ga ₂ O ₃ . Applied Physics Letters, 2018, 112, .	3.3	196
32	Band gap maps beyond the delocalization limit: correlation between optical band gaps and plasmon energies at the nanoscale. Scientific Reports, 2018, 8, 848.	3.3	20
33	Optical properties of an ensemble of G-centers in silicon. Physical Review B, 2018, 97, .	3.2	49
34	Sb-related defects in Sb-doped ZnO thin film grown by pulsed laser deposition. Journal of Applied Physics, 2018, 123, .	2.5	19
35	Reply to Comment on "Nanoscale mapping of optical band gaps using monochromated electron energy loss spectroscopy". Nanotechnology, 2018, 29, 318002.	2.6	0
36	Phase stability and strain accumulation in CdO as a function of Cd/O supply during MOVPE synthesis. Superlattices and Microstructures, 2018, 120, 569-577.	3.1	0

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37	Bandgap and band edge positions in compositionally graded ZnCdO. Journal of Applied Physics, 2018, 124, .	2.5	5
38	GaN-VZn acceptor complex defect in Ga-doped ZnO. Science China: Physics, Mechanics and Astronomy, 2018, 61, 1.	5.1	6
39	Limitation of Na-H codoping in achieving device-quality p-type ZnO. Materials Science in Semiconductor Processing, 2017, 69, 28-31.	4.0	6
40	Nanoscale mapping of optical band gaps using monochromated electron energy loss spectroscopy. Nanotechnology, 2017, 28, 105703.	2.6	15
41	Micro-structured inverted pyramid texturization of Si inspired by self-assembled Cu nanoparticles. Nanoscale, 2017, 9, 907-914.	5.6	59
42	18.87%-efficient inverted pyramid structured silicon solar cell by one-step Cu-assisted texturization technique. Solar Energy Materials and Solar Cells, 2017, 166, 121-126.	6.2	76
43	Surface localization of the Er-related optical active centers in Er doped zinc oxide films. Journal of Applied Physics, 2017, 121, .	2.5	8
44	Improvements in Realizing 4H-SiC Thermal Neutron Detectors. EPJ Web of Conferences, 2016, 106, 05004.	0.3	9
45	Self-diffusion measurements in isotopic heterostructures of undoped and in situ doped ZnO: Zinc vacancy energetics. Physical Review B, 2016, 94, .	3.2	17
46	Oxygen vacancies: The origin of n -type conductivity in ZnO. Physical Review B, 2016, 93, .	3.2	244
47	4H-SiC Neutron Sensors Based on Ion Implanted ^{10}B Neutron Converter Layer. IEEE Transactions on Nuclear Science, 2016, 63, 1976-1980.	2.0	10
48	Interface Engineering of High Efficiency Organic-Silicon Heterojunction Solar Cells. ACS Applied Materials & Interfaces, 2016, 8, 26-30.	8.0	35
49	Germanium-based quantum emitters towards a time-reordering entanglement scheme with degenerate exciton and biexciton states. Physical Review B, 2015, 91, .	3.2	16
50	Maskless inverted pyramid texturization of silicon. Scientific Reports, 2015, 5, 10843.	3.3	87
51	Fluorine doping: a feasible solution to enhancing the conductivity of high-resistance wide bandgap $\text{Mg}_{0.51}\text{Zn}_{0.49}\text{O}$ active components. Scientific Reports, 2015, 5, 15516.	3.3	16
52	Optical activity and defect/dopant evolution in ZnO implanted with Er. Journal of Applied Physics, 2015, 118, .	2.5	30
53	4H-SiC neutron sensors based on ion implanted ^{10}B neutron converter layer. , 2015, , .		1
54	Back-illuminated Si photocathode: a combined experimental and theoretical study for photocatalytic hydrogen evolution. Energy and Environmental Science, 2015, 8, 650-660.	30.8	76

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55	Beryllium sites in MBE-grown BeZnO alloy films. Journal Physics D: Applied Physics, 2014, 47, 175102.	2.8	17
56	Crucial role of implanted atoms on dynamic defect annealing in ZnO. Applied Physics Letters, 2014, 104, .	3.3	24
57	Enhancement-mode ZnO/Mg _{0.5} Zn _{0.5} O HFET on Si. Journal Physics D: Applied Physics, 2014, 47, 255101.	2.8	16
58	Effect of implanted species on thermal evolution of ion-induced defects in ZnO. Journal of Applied Physics, 2014, 115, .	2.5	43
59	Tunneling in ZnO/ZnCdO quantum wells towards next generation photovoltaic cells. Solar Energy, 2014, 106, 82-87.	6.1	10
60	Radiation Silicon Carbide Detectors Based on Ion Implantation of Boron. IEEE Transactions on Nuclear Science, 2014, 61, 2105-2111.	2.0	23
61	Effects of temperature, triazole and hot-pressing on the performance of TiO ₂ photoanode in a solid-state photoelectrochemical cell. Electrochimica Acta, 2014, 115, 66-74.	5.2	10
62	Probing Defects in Nitrogen-Doped Cu ₂ O. Scientific Reports, 2014, 4, 7240.	3.3	96
63	Influence of graphene synthesizing techniques on the photocatalytic performance of graphene-TiO ₂ nanocomposites. Physical Chemistry Chemical Physics, 2013, 15, 15528-15537.	2.8	43
64	Bulk Growth and Impurities. Semiconductors and Semimetals, 2013, 88, 67-104.	0.7	7
65	Interplay of dopants and native point defects in ZnO. Physica Status Solidi (B): Basic Research, 2013, 250, 2110-2113.	1.5	11
66	Diffusion and configuration of Li in ZnO. Journal of Applied Physics, 2013, 113, 023702.	2.5	23
67	Intrinsic Point-Defect Balance in Self-Ion-Implanted ZnO. Physical Review Letters, 2013, 110, 015501.	7.8	28
68	Selective nano-emitter fabricated by silver assisted chemical etch-back for multicrystalline solar cells. RSC Advances, 2013, 3, 15483.	3.6	16
69	First tests of silicon-carbide semiconductors as candidate neutron detector for the ITER Test Blanket Modules. , 2013, , .		7
70	CdO/ZnO multiple quantum wells as components for next generation solar cells. , 2013, , .		1
71	On the interplay of point defects and Cd in non-polar ZnCdO films. Journal of Applied Physics, 2013, 113, 023512.	2.5	7
72	Solid-state photoelectrochemical H ₂ generation with gaseous reactants. Electrochimica Acta, 2013, 97, 320-325.	5.2	32

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73	Nano-structuring in SiGe by oxidation induced anisotropic Ge self-organization. Journal of Applied Physics, 2013, 113, 104310.	2.5	11
74	Impurity Sublattice Localization in ZnO Revealed by Li Marker Diffusion. Physical Review Letters, 2013, 110, 175503.	7.8	15
75	Carrier dynamics in linearly and step graded bandgap Zn _{1-x} CdxO structures. Applied Physics Letters, 2013, 102, .	3.3	3
76	Engineering of optically defect free Cu ₂ O enabling exciton luminescence at room temperature. Optical Materials Express, 2013, 3, 2072.	3.0	38
77	Prediction of high efficiency ZnMgO/Si solar cells suppressing carrier recombination by conduction band engineering. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 585-588.	1.8	43
78	Anomalous Diffusion of Intrinsic Defects in K ⁺ Implanted ZnO using Li as Tracer. Materials Research Society Symposia Proceedings, 2012, 1394, 75.	0.1	2
79	Ge concentrations in pile-up layers of sub-100-nm SiGe films for nano-structuring by thermal oxidation. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, .	1.2	14
80	Temperature dependence of Cu ₂ O orientations in the oxidation of Cu (111)/ZnO (0001) by oxygen plasma. Chinese Physics B, 2012, 21, 076401.	1.4	8
81	Ge redistribution in SiO ₂ /SiGe structures under thermal oxidation: Dynamics and predictions. Journal of Applied Physics, 2012, 111, .	2.5	18
82	Zinc vacancy and oxygen interstitial in ZnO revealed by sequential annealing and electron irradiation. Physical Review B, 2012, 86, .	3.2	139
83	Testing ZnO based photoanodes for PEC applications. Energy Procedia, 2012, 22, 101-107.	1.8	11
84	A comparative analysis of oxidation rates for thin films of SiGe versus Si. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1934-1939.	1.8	7
85	Annealing of ion implanted CdZnO. Journal Physics D: Applied Physics, 2012, 45, 235304.	2.8	13
86	Control of Li configuration and electrical properties of Li-doped ZnO. Journal Physics D: Applied Physics, 2012, 45, 375301.	2.8	12
87	Thermal process dependence of Li configuration and electrical properties of Li-doped ZnO. Applied Physics Letters, 2012, 100, 042107.	3.3	33
88	Impurity-limited lattice disorder recovery in ion-implanted ZnO. Applied Physics Letters, 2012, 101, .	3.3	14
89	Native point defects at ZnO surfaces, interfaces and bulk films. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1566-1569.	0.8	16
90	Time-resolved spectroscopy of carrier dynamics in graded ZnCdxO multilayer structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1805-1808.	0.8	1

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91	Nanostructure Formation and Passivation of Large Area Black Silicon for Solar Cell Applications. Small, 2012, 8, 1392-1397.	10.0	137
92	Engineering of nearly strain-free ZnO films on Si(111) by tuning AlN buffer thickness. Physica B: Condensed Matter, 2012, 407, 1476-1480.	2.7	4
93	Temperature dependence of surface plasmon mediated near band-edge emission from Ag/ZnO nanorods. Journal of Optics (United Kingdom), 2011, 13, 075003.	2.2	1
94	H passivation of Li on Zn-site in ZnO: Positron annihilation spectroscopy and secondary ion mass spectrometry. Physical Review B, 2011, 84, .	3.2	22
95	Cd diffusion and thermal stability of CdZnO/ZnO heterostructures. Applied Physics Letters, 2011, 99, .	3.3	17
96	Identification of substitutional Li in ZnO and its role as an acceptor. Physical Review B, 2011, 83, .	3.2	54
97	Surface/strain energy balance controlling preferred orientation in CdZnO films. Journal of Applied Physics, 2011, 110, .	2.5	8
98	Understanding phase separation in ZnCdO by a combination of structural and optical analysis. Physical Review B, 2011, 83, .	3.2	52
99	Tuning light absorption by band gap engineering in ZnCdO as a function of MOVPE-synthesis conditions and annealing. Journal of Crystal Growth, 2011, 315, 301-304.	1.5	25
100	On the mechanism of enhanced photocatalytic activity of composite TiO ₂ /carbon nanofilms. Applied Catalysis B: Environmental, 2011, 106, 337-342.	20.2	24
101	Li and OH-Li Complexes in Hydrothermally Grown Single-Crystalline ZnO. Journal of Electronic Materials, 2011, 40, 429-432.	2.2	11
102	Defect evolution and impurity migration in Na-implanted ZnO. Physical Review B, 2011, 84, .	3.2	28
103	Thermally induced surface instability in ion-implanted Mg-doped ZnO films. Physical Review B, 2011, 84, .	3.2	10
104	Effect of composition on damage accumulation in ternary ZnO-based oxides implanted with heavy ions. Journal of Applied Physics, 2010, 108, 033509.	2.5	17
105	Changing vacancy balance in ZnO by tuning synthesis between zinc/oxygen lean conditions. Journal of Applied Physics, 2010, 108, 046101.	2.5	14
106	Deep level related photoluminescence in ZnMgO. Applied Physics Letters, 2010, 97, .	3.3	71
107	Stabilization of Ge-rich defect complexes originating from E_c centers in $\text{Si}_{1-x}\text{Mg}_x\text{ZnO}$ films. Physical Review B, 2010, 81, .	3.2	14
108	High Zn Content Single-phase RS-MgZnO Suitable for Solar-blind Frequency Applications. , 2010, .		1

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109	An investigation of Fe-doped ZnO thin films grown by magnetron sputtering. Physica Scripta, 2010, T141, 014004.	2.5	6
110	Alloy-fluctuation-induced exciton localization in high-Mg-content (0.27 \times 0.55) wurtzite Mg _x Zn _{1-x} O epilayers. Journal Physics D: Applied Physics, 2010, 43, 285402.	2.8	15
111	Vacancy defect and defect cluster energetics in ion-implanted ZnO. Physical Review B, 2010, 81, .	3.2	121
112	Transportation of Na and Li in Hydrothermally Grown ZnO. Materials Research Society Symposia Proceedings, 2009, 1201, 1.	0.1	0
113	Controlled Growth of High-Quality ZnO-Based Films and Fabrication of Visible-Blind and Solar-Blind Ultra-Violet Detectors. Advanced Materials, 2009, 21, 4625-4630.	21.0	239
114	Correlation between nitrogen and carbon incorporation into MOVPE ZnO at various oxidizing conditions. Microelectronics Journal, 2009, 40, 232-235.	2.0	9
115	Zinc oxide: bulk growth, role of hydrogen and Schottky diodes. Journal Physics D: Applied Physics, 2009, 42, 153001.	2.8	74
116	Effect of spatial defect distribution on the electrical behavior of prominent vacancy point defects in swift-ion implanted Si. Physical Review B, 2009, 79, .	3.2	17
117	Interaction between Na and Li in ZnO. Applied Physics Letters, 2009, 95, 242111.	3.3	17
118	Schottky contacts to hydrogen doped ZnO. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1998-2001.	1.8	8
119	Common point defects in as-grown ZnO substrates studied by optical detection of magnetic resonance. Journal of Crystal Growth, 2008, 310, 1006-1009.	1.5	4
120	Structural and optical properties of polar and non-polar ZnO films grown by MOVPE. Journal of Crystal Growth, 2008, 310, 5020-5024.	1.5	17
121	Temperature dependence and decay times of zinc and oxygen vacancy related photoluminescence bands in zinc oxide. Solid State Communications, 2008, 145, 321-326.	1.9	121
122	Ion implantation in 4H-SiC. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1367-1372.	1.4	15
123	Formation and origin of the dominating electron trap in irradiated p -type silicon. Physical Review B, 2008, 78, .	3.2	20
124	Vacancy clustering and acceptor activation in nitrogen-implanted ZnO. Physical Review B, 2008, 77, .	3.2	63
125	Deuterium diffusion and trapping in hydrothermally grown single crystalline ZnO. Applied Physics Letters, 2008, 93, .	3.3	42
126	Effect of growth temperature on the characteristics of ZnO films grown on Si(111) substrates by metal-organic chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 224-227.	2.1	3

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127	Hydrothermally Grown Single-Crystalline Zinc Oxide; Characterization and Modification. Materials Research Society Symposia Proceedings, 2007, 1035, 1.	0.1	5
128	Millisecond processing beyond chip technology: From electronics to photonics. , 2007, , .		3
129	Recombination centers in as-grown and electron-irradiated ZnO substrates. Journal of Applied Physics, 2007, 102, 093504.	2.5	18
130	Excess vacancies in high energy ion implanted SiGe. Journal of Applied Physics, 2007, 101, 033508.	2.5	12
131	Hydrogen Migration in Single Crystalline ZnO. Materials Research Society Symposia Proceedings, 2007, 1035, 1.	0.1	1
132	Structural and optical properties of ZnO \hat{w} Mg \hat{w} 0.1Zn \hat{w} 0.9O multiple quantum wells grown on ZnO substrates. Applied Physics Letters, 2007, 90, 211909.	3.3	35
133	Carrier concentration and shallow electron states in Sb-doped hydrothermally grown ZnO. Superlattices and Microstructures, 2007, 42, 294-298.	3.1	4
134	Scanning spreading resistance microscopy of defect engineered low dose SIMOX samples. Microelectronic Engineering, 2007, 84, 547-550.	2.4	1
135	Visualization of MeV ion impacts in Si using scanning capacitance microscopy. Physical Review B, 2006, 73, .	3.2	13
136	Ion Implantation Processing and Related Effects in SiC. Materials Science Forum, 2006, 527-529, 781-786.	0.3	11
137	Identification of oxygen and zinc vacancy optical signals in ZnO. Applied Physics Letters, 2006, 89, 262112.	3.3	387
138	Deactivation of Li by vacancy clusters in ion-implanted and flash-annealed ZnO. Physical Review B, 2006, 74, .	3.2	52
139	Annealing study of hydrothermally grown ZnO wafers. Physica Scripta, 2006, T126, 10-14.	2.5	13
140	Scanning probe microscopy of single Au ion implants in Si. Materials Science and Engineering C, 2006, 26, 782-787.	7.3	0
141	Si-based Materials for Advanced Microelectronic Devices: Synthesis, Defects and Diffusion. Nuclear Instruments & Methods in Physics Research B, 2006, 253, vii-viii.	1.4	0
142	Vacancy-impurity pairs in relaxedSi \hat{w} 1 \hat{w} xGe \hat{w} layers studied by positron annihilation spectroscopy. Physical Review B, 2006, 73, .	3.2	13
143	Development of radiation tolerant semiconductor detectors for the Super-LHC. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2005, 546, 99-107.	1.6	29
144	Recent advancements in the development of radiation hard semiconductor detectors for S-LHC. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2005, 552, 7-19.	1.6	33

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145	Carrier concentration and shallow electron states in In-doped hydrothermally grown ZnO. Superlattices and Microstructures, 2005, 38, 364-368.	3.1	5
146	Palladium Schottky barrier contacts to the (0001 $\bar{1}$,-) and (101 $\bar{1}$,0)-face of hydrothermally grown n-ZnO. AIP Conference Proceedings, 2005, . .	0.4	3
147	Defect Behaviour in Deuterated and Non-Deuterated n-Type Si. Solid State Phenomena, 2005, 108-109, 553-560.	0.3	2
148	Capacitance spectroscopy study of InAs quantum dots and dislocations in p-GaAs matrix. AIP Conference Proceedings, 2005, . .	0.4	0
149	Fluence, flux, and implantation temperature dependence of ion-implantation-induced defect production in 4H \bar{c} -SiC. Journal of Applied Physics, 2005, 97, 033513.	2.5	26
150	Hydrogen implantation into ZnO for n ⁺ -layer formation. Applied Physics Letters, 2005, 87, 191910.	3.3	28
151	Vacancy-related defect distributions in ¹¹ B-, ¹⁴ N-, and ²⁷ Al-implanted 4H \bar{c} -SiC: Role of channeling. Journal of Applied Physics, 2004, 95, 57-63.	2.5	12
152	Palladium Schottky barrier contacts to hydrothermally grown n-ZnO and shallow electron states. Applied Physics Letters, 2004, 85, 2259-2261.	3.3	75
153	Divacancy annealing in Si: Influence of hydrogen. Physical Review B, 2004, 69, .	3.2	26
154	Optical Investigation of the Built-In Strain in 3C-SiC Epilayers. Materials Science Forum, 2004, 457-460, 657-660.	0.3	4
155	Spatial distribution of cavities in silicon formed by ion implantation generated excess vacancies. Journal of Applied Physics, 2004, 95, 4738-4741.	2.5	11
156	Sb lattice diffusion in Si ^{1-x} Ge ^x /Si(001) heterostructures: ϵ -Chemical and stress effects. Physical Review B, 2004, 69, .	3.2	22
157	Electronic structure of the phosphorus-vacancy complex in silicon: A resonant-bond model. Physical Review B, 2004, 70, .	3.2	12
158	Formation and stability of radiation defect complexes in Si and Si:Ge: Composition and pressure effects. Nuclear Instruments & Methods in Physics Research B, 2003, 202, 107-113.	1.4	9
159	Influence of doping on thermal stability of Si/Si ^{1-x} Ge ^x /Si heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 102, 53-57.	3.5	5
160	Phosphorus and boron diffusion in silicon under equilibrium conditions. Applied Physics Letters, 2003, 82, 2254-2256.	3.3	47
161	Vacancy-Type Defect Distributions of ¹¹ B-, ¹⁴ N- and ²⁷ Al-Implanted 4H-SiC Studied by Positron Annihilation Spectroscopy. Materials Science Forum, 2003, 433-436, 641-644.	0.3	2
162	Vacancy and interstitial depth profiles in ion-implanted silicon. Journal of Applied Physics, 2003, 93, 871-877.	2.5	22

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163	Vacancy-phosphorus complexes in strained Si _{1-x} Ge _x : Structure and stability. Physical Review B, 2003, 68, .	3.2	42
164	Diffusion of phosphorus in relaxed Si _{1-x} Ge _x films and strained Si/Si _{1-x} Ge _x heterostructures. Journal of Applied Physics, 2003, 94, 6533-6540.	2.5	30
165	Dynamic annealing in ion implanted SiC: Flux versus temperature dependence. Journal of Applied Physics, 2003, 94, 7112-7115.	2.5	44
166	Implanted p+n-Junctions in Silicon Carbide. AIP Conference Proceedings, 2003, , .	0.4	0
167	Influence of boron on radiation enhanced diffusion of antimony in delta-doped silicon. Journal of Applied Physics, 2002, 91, 4073-4077.	2.5	9
168	Ion mass effect on vacancy-related deep levels in Si induced by ion implantation. Physical Review B, 2002, 65, .	3.2	40
169	Characterization of Al-implanted 4H SiC High Voltage Diodes. Physica Scripta, 2002, T101, 207.	2.5	2
170	Phosphorus diffusion in silicon; influence of annealing conditions. Materials Research Society Symposia Proceedings, 2001, 669, 1.	0.1	2
171	Determination of parameters for channeling of protons in SiC polytype crystals in the backscattering geometry. Nuclear Instruments & Methods in Physics Research B, 2001, 184, 319-326.	1.4	12
172	Phosphorus Diffusion in Si _{1-x} Ge _x . Defect and Diffusion Forum, 2001, 194-199, 709-716.	0.4	5
173	Diffusion of Dopants and Impurities in Device Structures of SiC, SiGe and Si. Defect and Diffusion Forum, 2001, 194-199, 597-610.	0.4	1
174	Channeling Measurements of Ion Implantation Damage in 4H-SiC. Materials Science Forum, 2001, 353-356, 595-598.	0.3	0
175	Doping of Silicon Carbide by Ion Implantation. Materials Science Forum, 2001, 353-356, 549-554.	0.3	23
176	Vacancy-related deep levels in n-type Si _{1-x} Ge _x strained layers. Physical Review B, 2001, 63, .	3.2	21
177	Irradiation enhanced diffusion of boron in delta-doped silicon. Journal of Applied Physics, 2001, 89, 5400-5405.	2.5	9
178	Structural Defects in Ion Implanted 4H-SiC Epilayers. Materials Research Society Symposia Proceedings, 2000, 640, 1.	0.1	2
179	Thermal donor and antimony energy levels in relaxed Si _{1-x} Ge _x layers. Physical Review B, 2000, 61, 1708-1711.	3.2	1
180	Comparative study of divacancy and E-center electronic levels in Si and strained Si _{0.87} Ge _{0.13} layers. Journal of Applied Physics, 2000, 87, 4629-4631.	2.5	14

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181	Damage Evolution in Al-implanted 4H SiC. Materials Science Forum, 2000, 338-342, 869-872.	0.3	12
182	Channeled Implants in 6H Silicon Carbide. Materials Science Forum, 2000, 338-342, 889-892.	0.3	17
183	Damage Reduction in Channeled Ion Implanted 6H-SiC. Materials Science Forum, 2000, 338-342, 893-896.	0.3	13
184	Sb-enhanced diffusion in strained Si _{1-x} Ge _x : dependence on biaxial compression. Physical Review B, 1999, 59, 7274-7277.	3.2	21
185	Channeling implantations of Al ⁺ into 6H silicon carbide. Applied Physics Letters, 1999, 74, 3990-3992.	3.3	18
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